



## PJQ4442P-AU

### 40V N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

50 A

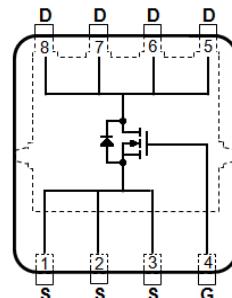
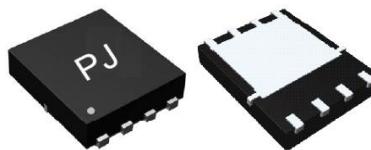
#### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ 10V$ ,  $I_D @ 20A < 7.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ 4.5V$ ,  $I_D @ 10A < 10.5m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams

DFN3333-8L



#### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	50	A
		32	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	200	
Power Dissipation	$P_D$	53.6	W
		26.8	
Continuous Drain Current	$I_D$	12.7	A
		10	
Power Dissipation	$P_D$	2.4	W
Power Dissipation		1.6	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~175	°C
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	2.8	°C/W
	Junction to Ambient	62.5	

- Limited only by Maximum Junction Temperature



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## Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.61	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	6.3	7.5	$m\Omega$
		$V_{GS}=4.5V, I_D=10A$	-	8	10.5	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	$nA$
<b>Dynamic</b> <sup>(Note 6)</sup>						
Total Gate Charge	$Q_g$	$V_{DS}=20V, I_D=10A,$ $V_{GS}=4.5V$ <sup>(Note 1,2)</sup>	-	17	-	$nC$
Gate-Source Charge	$Q_{gs}$		-	4.9	-	
Gate-Drain Charge	$Q_{gd}$		-	6.4	-	
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $f=1MHz$	-	1759	-	$pF$
Output Capacitance	$C_{oss}$		-	176	-	
Reverse Transfer Capacitance	$C_{rss}$		-	126	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A,$ $V_{GS}=10V, R_G=6\Omega$ <sup>(Note 1,2)</sup>	-	11	-	$ns$
Turn-On Rise Time	$t_r$		-	21	-	
Turn-Off Delay Time	$t_{d(off)}$		-	40	-	
Turn-Off Fall Time	$t_f$		-	25	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_s$	---	-	-	50	A
Diode Forward Voltage	$V_{SD}$	$I_s=1A, V_{GS}=0V$	-	0.7	1	V

### NOTES :

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$ .
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ C$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25^\circ C$ .
4. The maximum current rating is package limited.
5.  $R_{OJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



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## TYPICAL CHARACTERISTIC CURVES

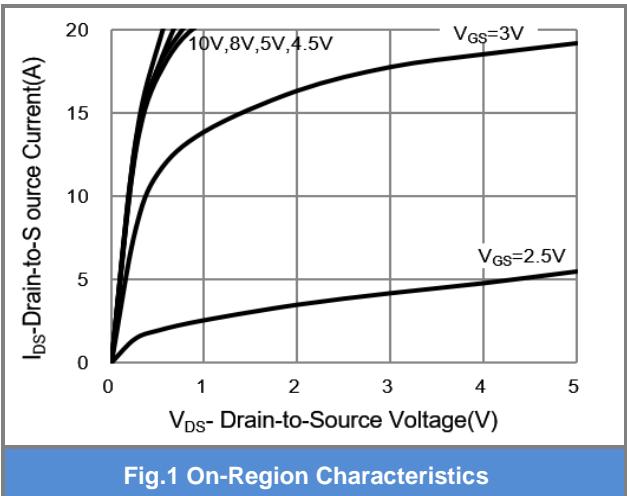


Fig.1 On-Region Characteristics

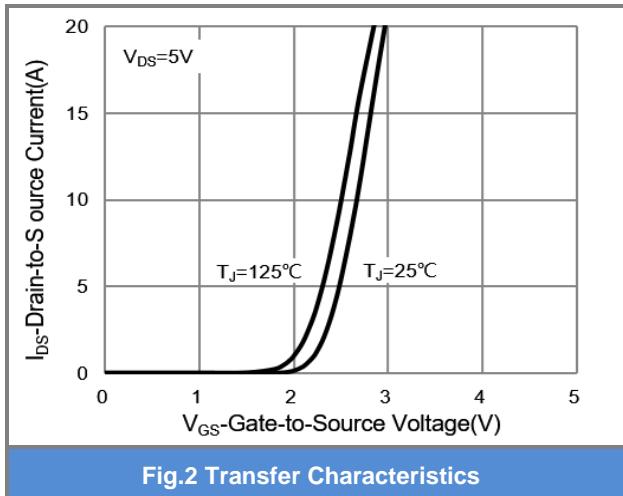


Fig.2 Transfer Characteristics

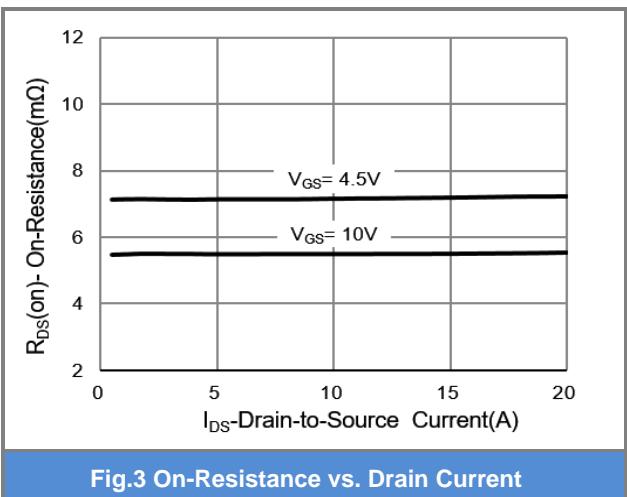


Fig.3 On-Resistance vs. Drain Current

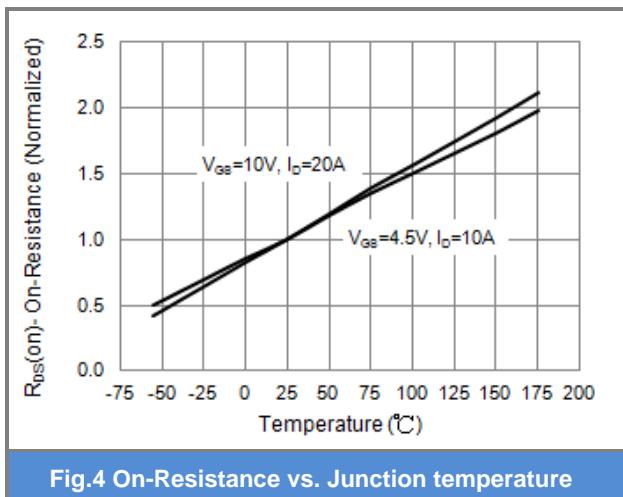


Fig.4 On-Resistance vs. Junction temperature

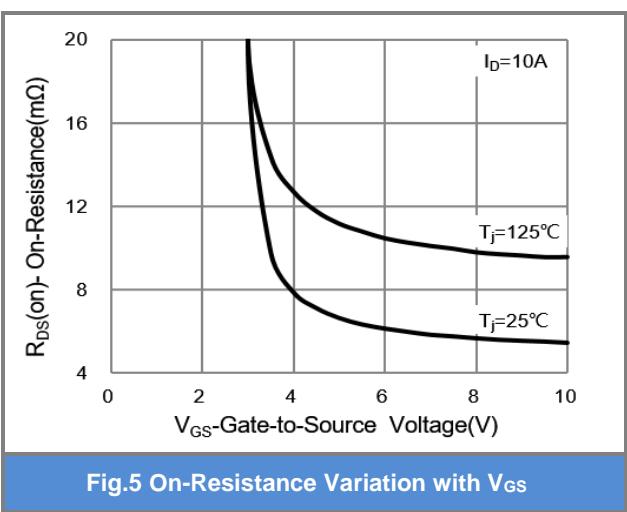


Fig.5 On-Resistance Variation with V\_GS

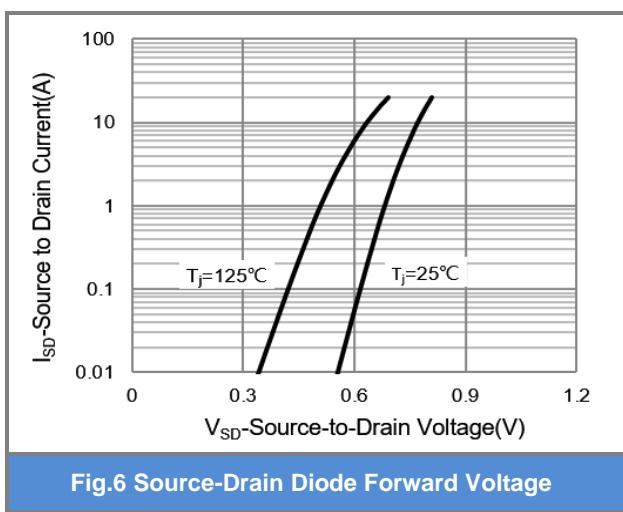


Fig.6 Source-Drain Diode Forward Voltage



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## TYPICAL CHARACTERISTIC CURVES

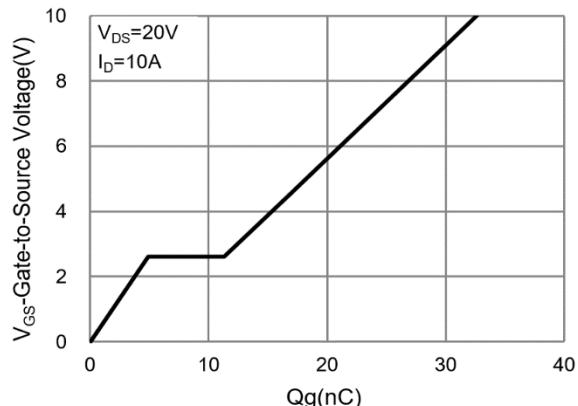


Fig.7 Gate-Charge Characteristics

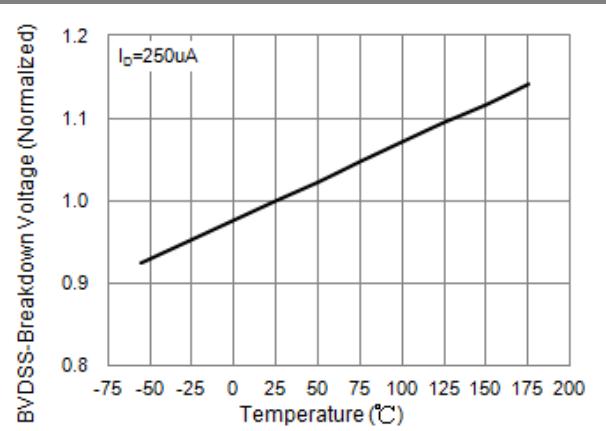


Fig.8 Breakdown Voltage Variation vs. Temperature

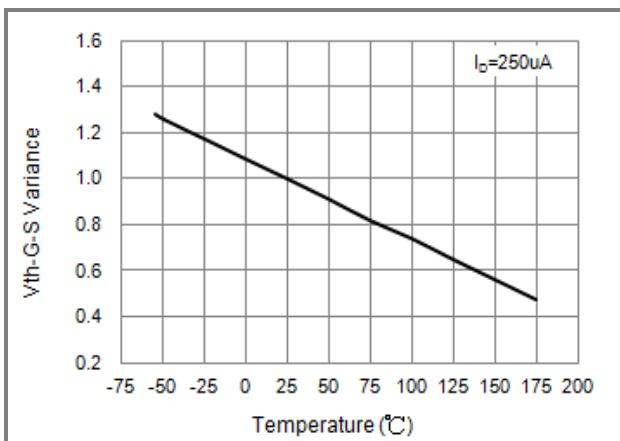


Fig.9 Threshold Voltage Variation with Temperature

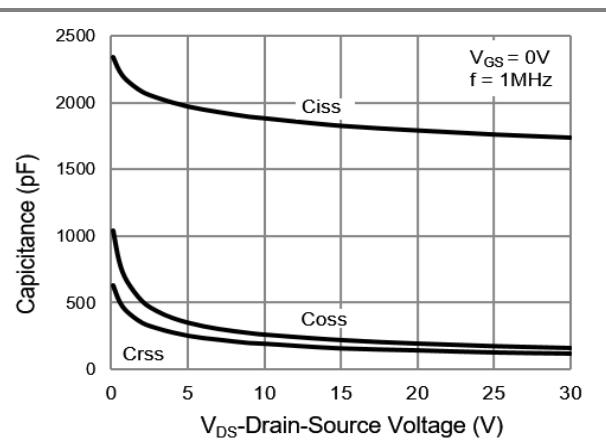


Fig.10 Capacitance vs. Drain-Source Voltage

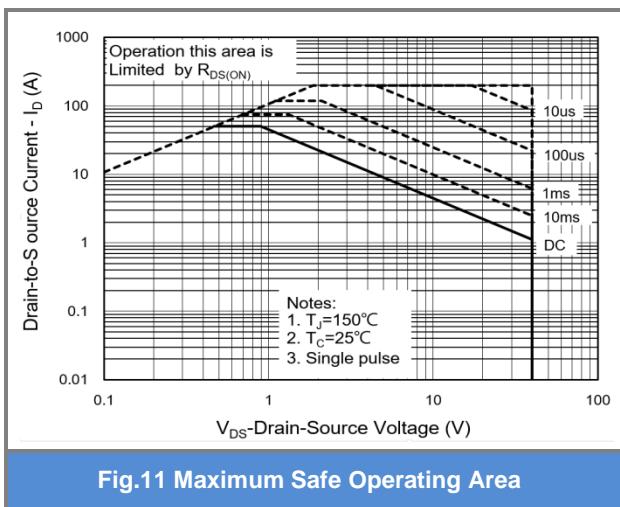


Fig.11 Maximum Safe Operating Area

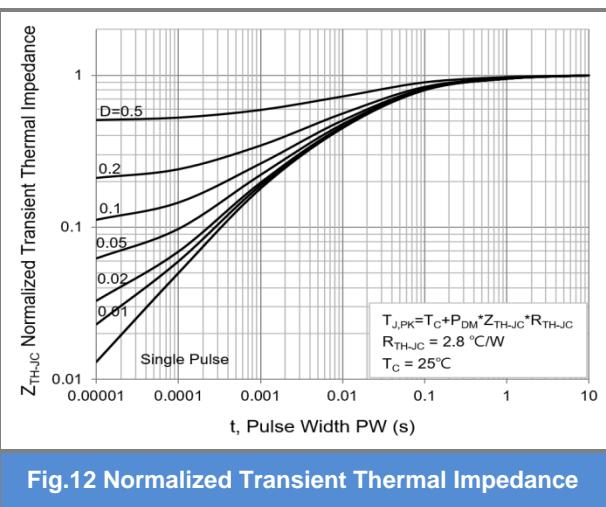


Fig.12 Normalized Transient Thermal Impedance

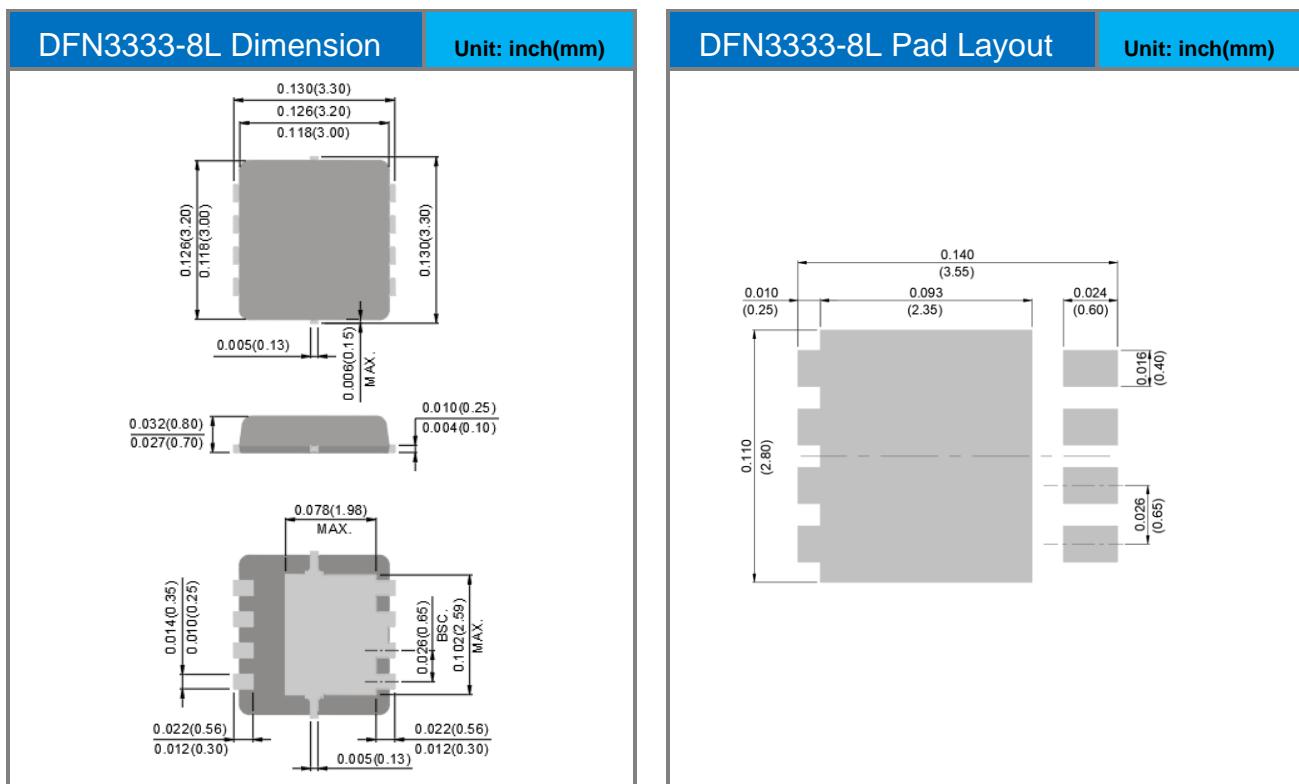


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## Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4442P-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4442	Halogen free RoHS compliant

## Packaging Information & Mounting Pad Layout





## **PJQ4442P-AU**

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